

#### **Features**

- · Trench Power LV MOSFET Technology
- · High Speed Switching
- High Density Cell Design for Low R<sub>DS(on)</sub>
- · Epoxy Meets UL 94 V-0 Flammability Rating
- · Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

## **Maximum Ratings**

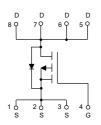
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 1.5°C/W Junction to Case

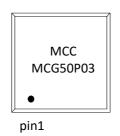
| Parameter                     | Symbol          | Rating | Unit |
|-------------------------------|-----------------|--------|------|
| Drain-Source Voltage          | V <sub>DS</sub> | -30    | V    |
| Gate-Source Volltage          | V <sub>GS</sub> | ±25    | V    |
| Continuous Drain Current      | I <sub>D</sub>  | -50    | Α    |
| Pulsed Drain Current (Note 2) | I <sub>DM</sub> | -200   | Α    |
| Avalanche Energy              | E <sub>AS</sub> | 73     | mJ   |
| Total Power Dissipation       | P <sub>D</sub>  | 83     | W    |

Note: 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

2. Pulse Test: Pulse Width≤300µs,Duty cycle ≤2%.

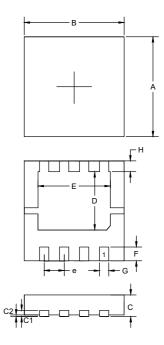
## **Internal Structure and Marking Code**





# P-CHANNEL MOSFET

#### **DFN3333**



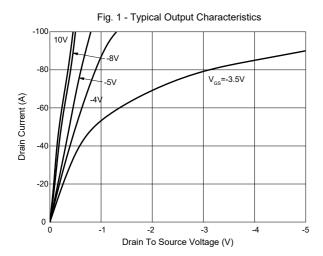
|       | DIMENSIONS |       |      |      |      |  |
|-------|------------|-------|------|------|------|--|
| DIM   | INCHES     |       | MM   |      | NOTE |  |
| Dilvi | MIN        | MAX   | MIN  | MAX  | NOTE |  |
| Α     | 0.126      | 0.130 | 3.20 | 3.30 |      |  |
| В     | 0.126      | 0.130 | 3.20 | 3.30 |      |  |
| С     | 0.030      | 0.033 | 0.75 | 0.85 |      |  |
| C1    | 0.007      | 0.009 | 0.18 | 0.22 |      |  |
| C2    |            | 0.002 |      | 0.05 |      |  |
| D     | 0.071      | 0.079 | 1.80 | 2.00 |      |  |
| Е     | 0.087      | 0.098 | 2.20 | 2.50 |      |  |
| F     | 0.016      | 0.020 | 0.40 | 0.50 |      |  |
| G     | 0.010      | 0.014 | 0.25 | 0.35 |      |  |
| Н     | 0.012      | 0.016 | 0.30 | 0.40 |      |  |
| е     | 0.024      | 0.028 | 0.60 | 0.70 |      |  |

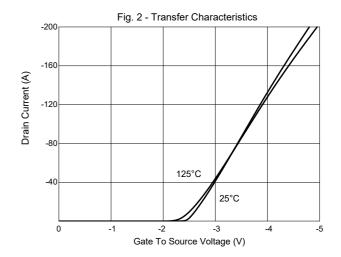


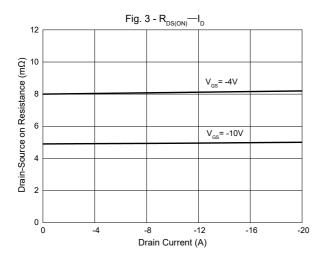
## Electrical Characteristics @ 25°C (Unless Otherwise Specified)

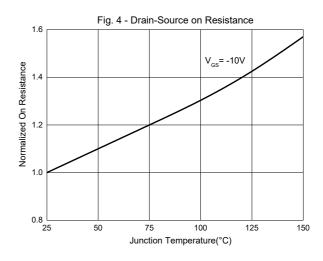
| Parameter                       | Symbol               | Test Conditions  | Min  | Тур   | Max  | Unit |  |
|---------------------------------|----------------------|--|------|-------|------|------|--|
| Static Characteristics          |                      |  |      |       |      |      |  |
| Drain-Source Breakdown Voltage  | V <sub>(BR)DSS</sub> | V <sub>GS</sub> =0V, I <sub>D</sub> =-250µA                      | -30  |       |      | V    |  |
| Gate-Source Leakage Current     | I <sub>GSS</sub>     | V <sub>DS</sub> =0V, V <sub>GS</sub> =±25V                       |      |       | ±100 | nA   |  |
| Zero Gate Voltage Drain Current | I <sub>DSS</sub>     | V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V                       |      |       | -1   | μA   |  |
| Gate-Threshold Voltage          | V <sub>GS(th)</sub>  | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA        | -1.2 | -1.8  | -2.8 | V    |  |
| Drain-Source On-Resistance      | В                    | V <sub>GS</sub> =-10V, I <sub>D</sub> =-15A                      |      | 5.0   | 6.2  | mΩ   |  |
| Dialit-Source Off-Resistance    | $R_{DS(on)}$         | V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A                     |      | 6.9   | 11   | mΩ   |  |
| Diode Characteristics           | ·                    |  | ·    |       |      |      |  |
| Continuous Body Diode Current   | Is                   |  |      |       | -50  | Α    |  |
| Diode Forward Voltage           | V <sub>SD</sub>      | V <sub>GS</sub> =0V, I <sub>S</sub> =-20A                        |      |       | -1.2 | V    |  |
| Reverse Recovery Time           | t <sub>rr</sub>      | I <sub>F</sub> =-20A, dI <sub>F</sub> /dt=100A/μs                |      | 24    |      | ns   |  |
| Reverse Recovery Charge         | Q <sub>rr</sub>      | 1;20A, dif/di-100/4µ3  |      | 8.5   |      | nC   |  |
| Dynamic Characteristics         |                      |  |      |       |      |      |  |
| Input Capacitance               | C <sub>iss</sub>     |  |      | 6464  |      | pF   |  |
| Output Capacitance              | C <sub>oss</sub>     | V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V,f=1MHz                 |      | 779   |      |      |  |
| Reverse Transfer Capacitance    | C <sub>rss</sub>     |  |      | 477   |      |      |  |
| Total Gate Charge               | Qg                   |  |      | 111.7 |      |      |  |
| Gate-Source Charge              | Q <sub>gs</sub>      | V <sub>DS</sub> =-15V,V <sub>GS</sub> =-10V,I <sub>D</sub> =-20A |      | 21.1  |      | nC   |  |
| Gate-Drain Charge               | $Q_{gd}$             |  |      | 22.9  |      |      |  |
| Turn-On Delay Time              | t <sub>d(on)</sub>   |  |      | 15    |      |      |  |
| Turn-On Rise Time               | t <sub>r</sub>       | V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V,                    |      | 79    |      | no   |  |
| Turn-Off Delay Time             | t <sub>d(off)</sub>  | $R_G=3\Omega$ , $I_{DS}=-20A$                                    |      | 136   |      | ns   |  |
| Turn-Off Fall Time              | t <sub>f</sub>       |  |      | 80    |      |      |  |

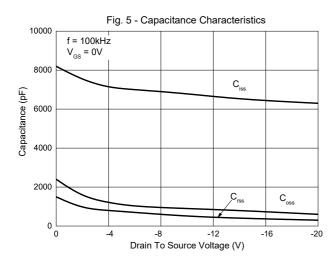


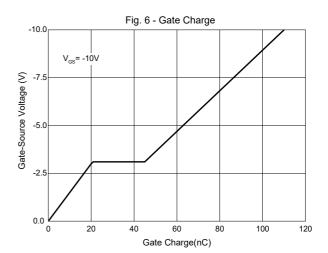




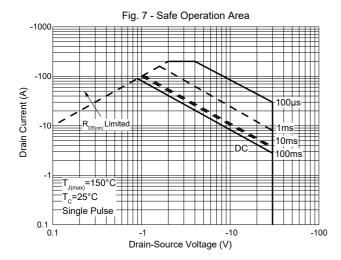


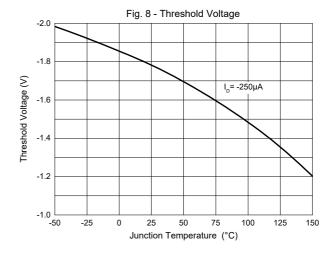


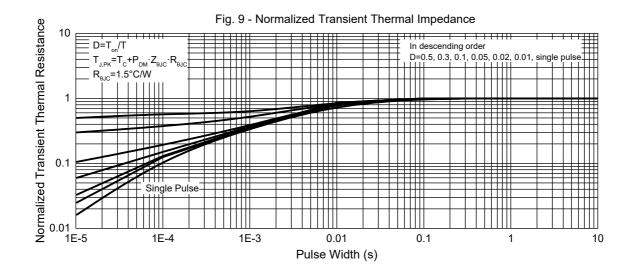














## **Ordering Information**

| Device         | Packing               |
|----------------|-----------------------|
| Part Number-TP | Tape&Reel: 5Kpcs/Reel |

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